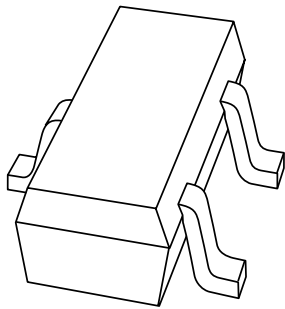


DATA SHEET



BFQ67T

NPN 8 GHz wideband transistor

Product specification
Supersedes data of 1999 Nov 02

2000 Mar 06

NPN 8 GHz wideband transistor

BFQ67T

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability
- SOT416 (SC-75) envelope.

APPLICATIONS

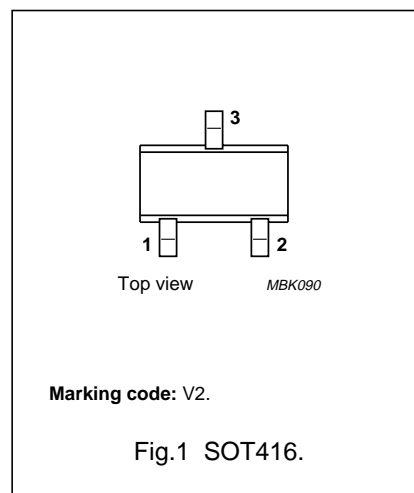
Wideband applications such as satellite TV tuners and RF portable communications equipment up to 2 GHz.

DESCRIPTION

NPN transistor in a plastic SOT416 (SC-75) package.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	–	10	V
I_C	collector current (DC)		–	–	50	mA
P_{tot}	total power dissipation	$T_s \leq 75\text{ °C}$; note 1	–	–	150	mW
h_{FE}	DC current gain	$I_C = 15\text{ mA}$; $V_{CE} = 5\text{ V}$; $T_j = 25\text{ °C}$	60	100	–	
f_T	transition frequency	$I_C = 15\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 2\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	8	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 15\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	13	–	dB
F	noise figure	$I_C = 5\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 1\text{ GHz}$	–	1.3	–	dB

Note

1. T_s is the temperature at the soldering point of the collector pin.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	10	V
V_{EBO}	emitter-base voltage	open collector	–	2.5	V
I_C	collector current (DC)		–	50	mA
P_{tot}	total power dissipation	$T_s \leq 75\text{ °C}$; note 1	–	150	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. T_s is the temperature at the soldering point of the collector pin.

NPN 8 GHz wideband transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	500	K/W

CHARACTERISTICS

$T_j = 25\text{ °C}$; unless otherwise specified.

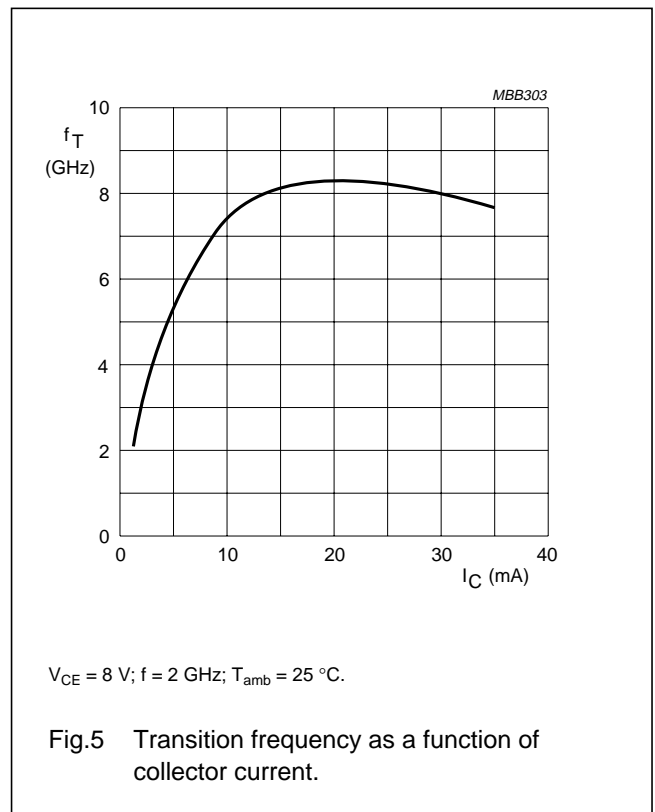
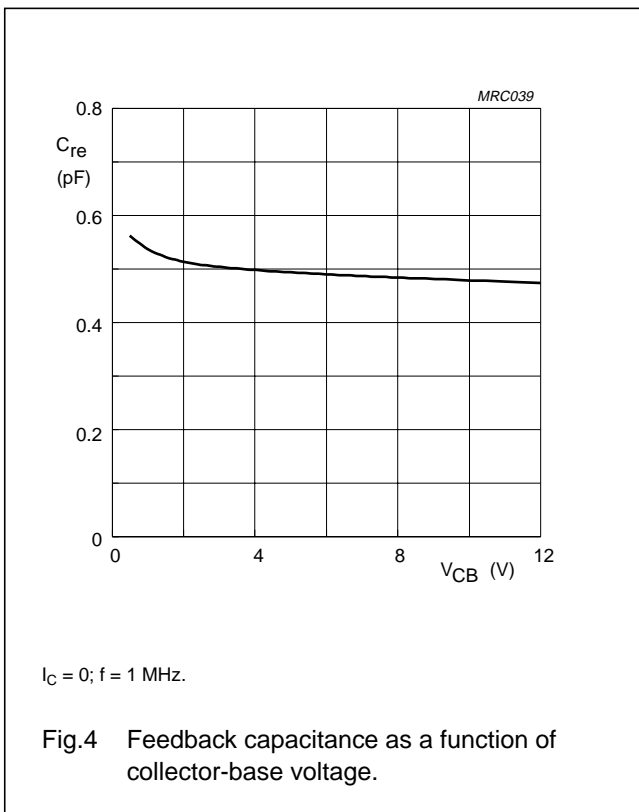
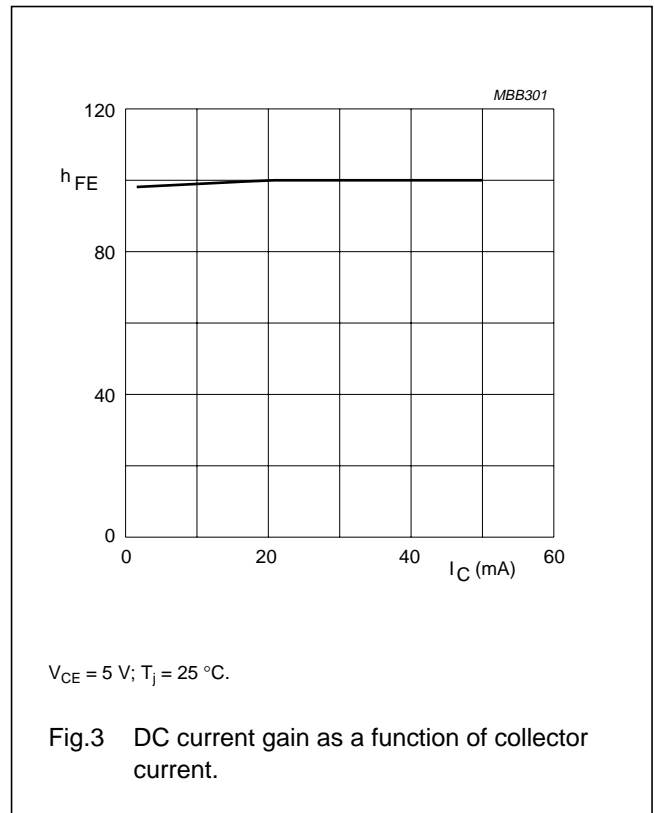
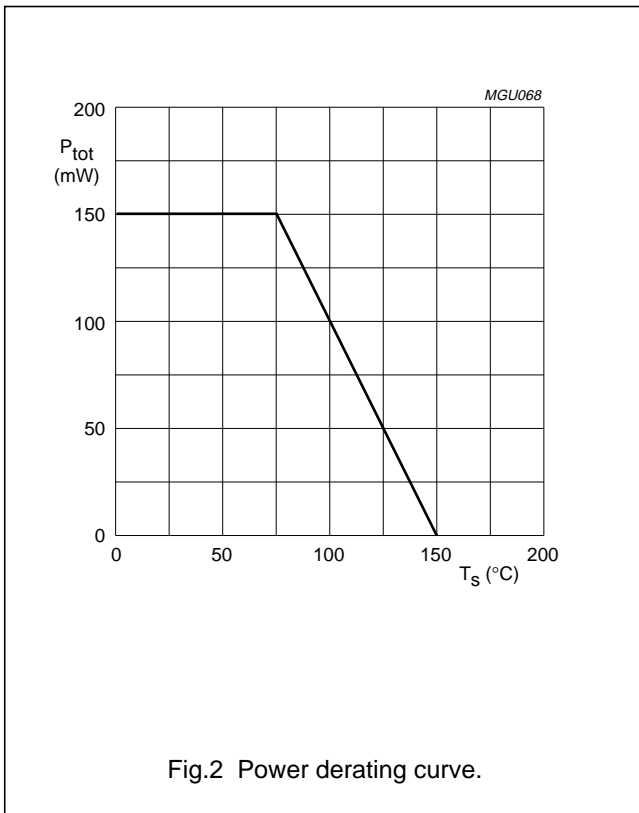
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 5\text{ V}$	–	–	50	nA
h_{FE}	DC current gain	$I_C = 15\text{ mA}$; $V_{CE} = 5\text{ V}$	60	100	–	
C_c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 8\text{ V}$; $f = 1\text{ MHz}$	–	0.7	–	pF
C_e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = 0.5\text{ V}$; $f = 1\text{ MHz}$	–	1.3	–	pF
C_{re}	feedback capacitance	$I_C = 0$; $V_{CE} = 8\text{ V}$; $f = 1\text{ MHz}$	–	0.5	–	pF
f_T	transition frequency	$I_C = 15\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 2\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	8	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 15\text{ mA}$; $V_{CE} = 8\text{ V}$; $T_{amb} = 25\text{ °C}$; note 1 $f = 1\text{ GHz}$ $f = 2\text{ GHz}$	– –	13 8	– –	dB dB
F	noise figure	$\Gamma_s = \Gamma_{opt}$; $I_C = 5\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 1\text{ GHz}$ $f = 2\text{ GHz}$	– –	1.3 2.2	– –	dB dB
		$\Gamma_s = \Gamma_{opt}$; $I_C = 15\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 1\text{ GHz}$ $f = 2\text{ GHz}$	– –	2 2.7	– –	dB dB
		$V_{CE} = 8\text{ V}$; $f = 2\text{ GHz}$; $Z_s = 60\ \Omega$; $I_C = 5\text{ mA}$ $I_C = 15\text{ mA}$	– –	2.5 3	– –	dB dB

Note

1. G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and $G_{UM} = 10 \log \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)}$ dB

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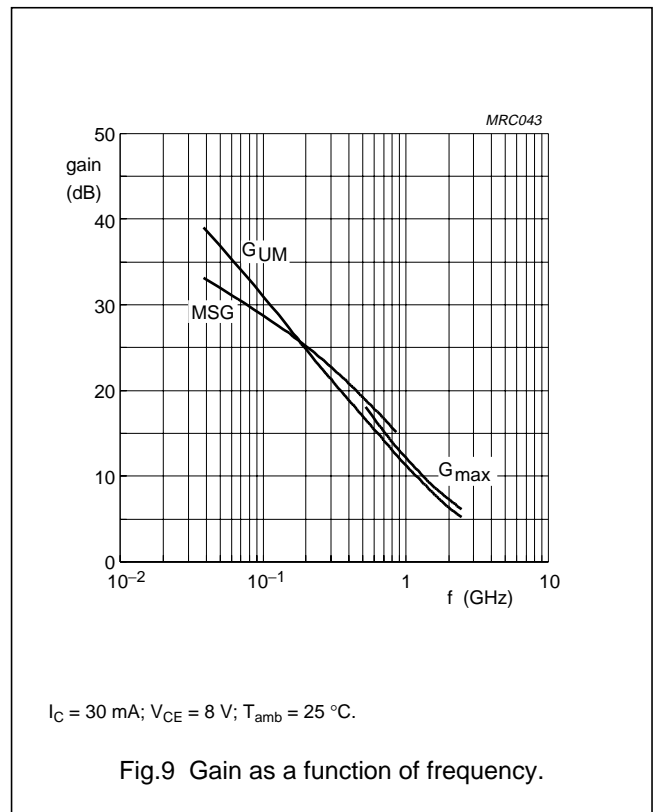
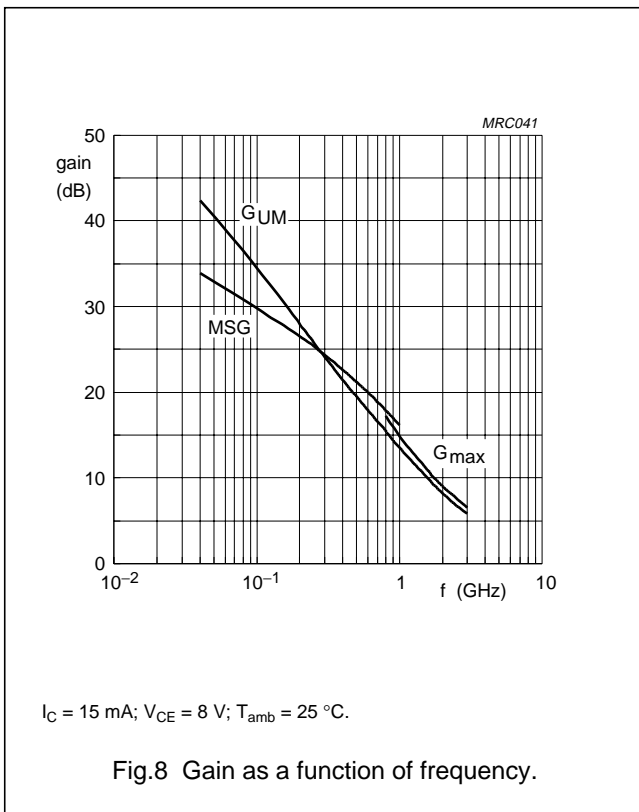
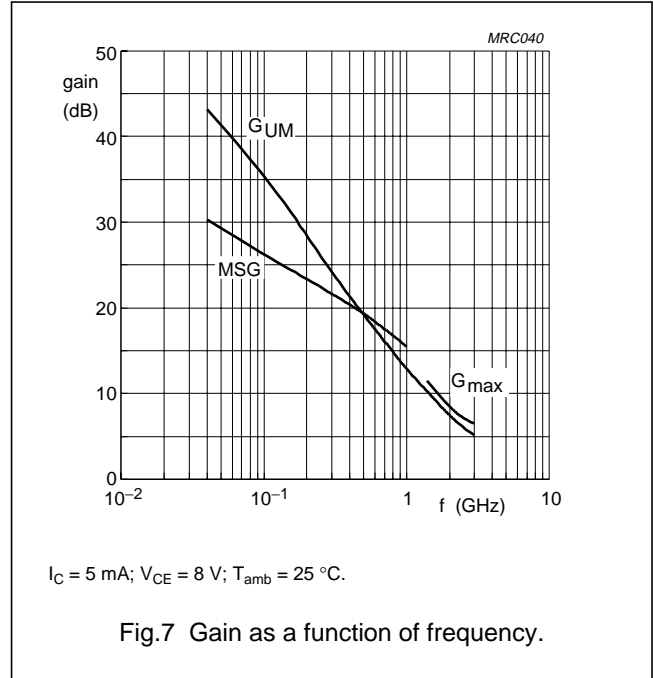
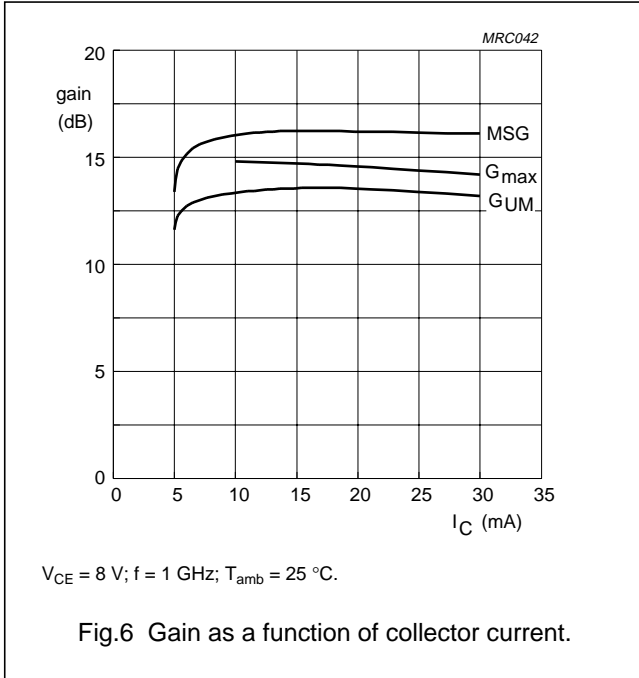
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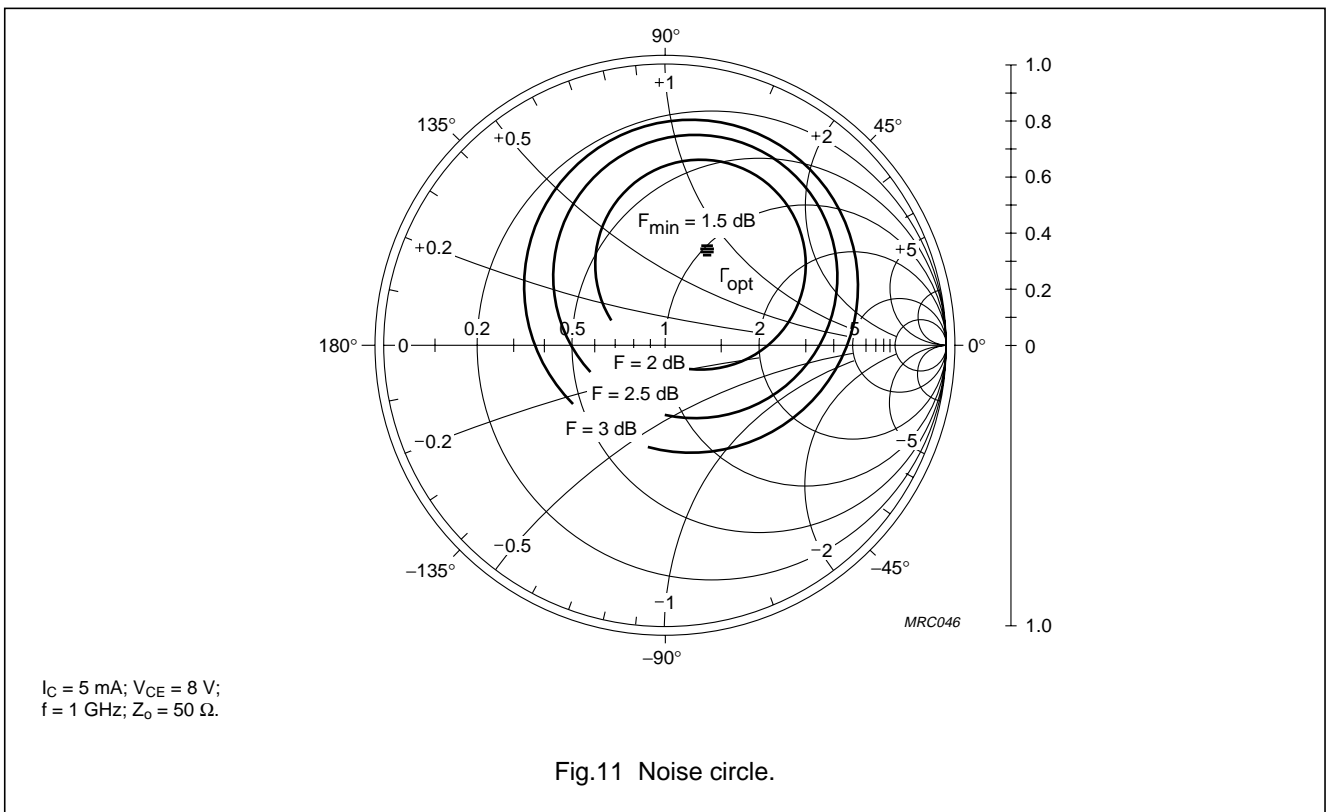
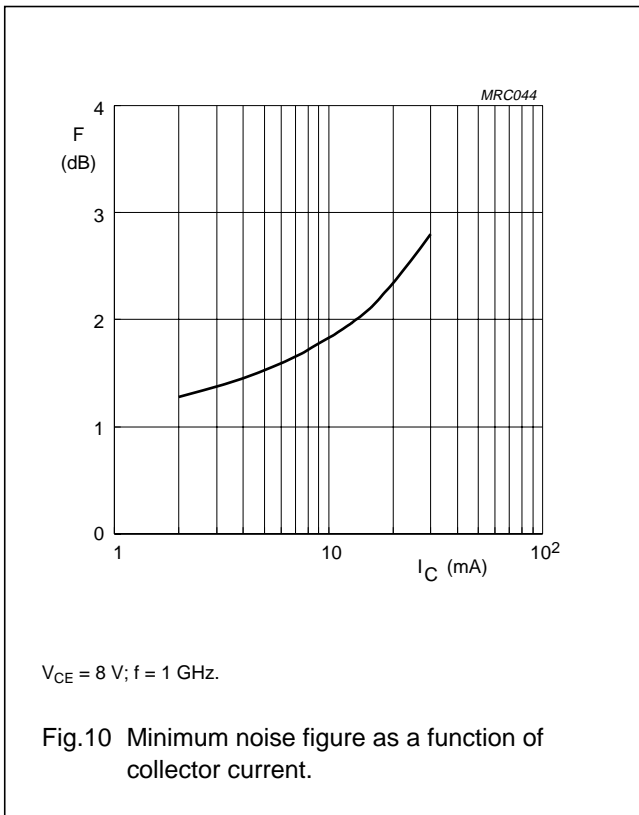
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In Figs 6 to 9, G_{UM} = maximum unilateral power gain; MSG = maximum stable gain; G_{max} = maximum available gain.



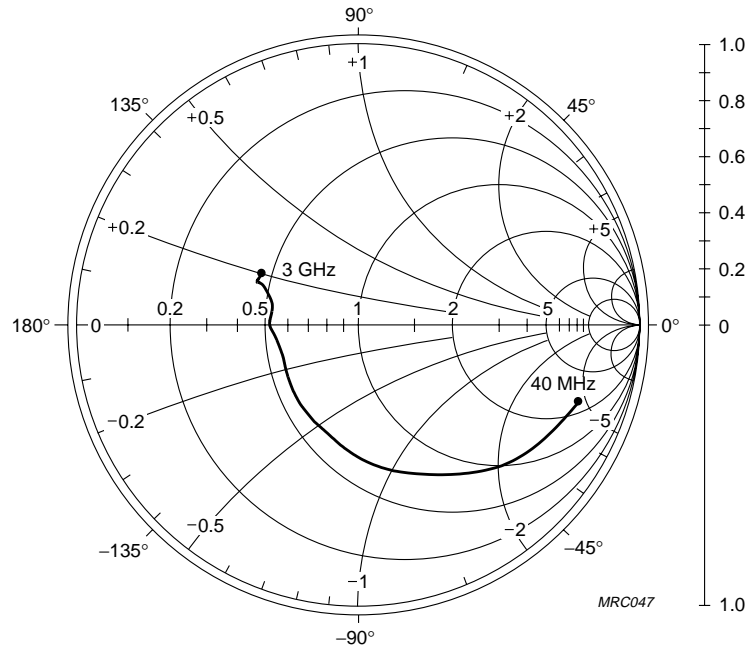
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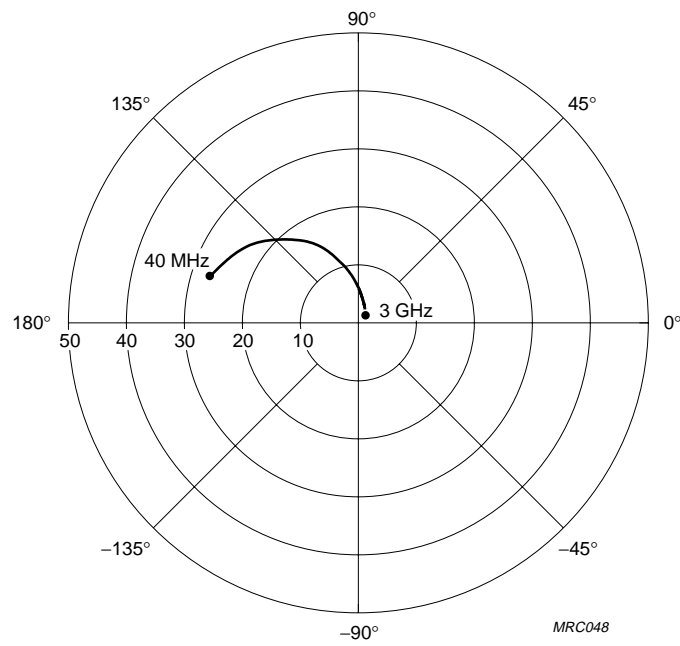
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$I_C = 15 \text{ mA}$; $V_{CE} = 8 \text{ V}$; $Z_o = 50 \Omega$.

Fig.12 Common emitter input reflection coefficient (S_{11}).

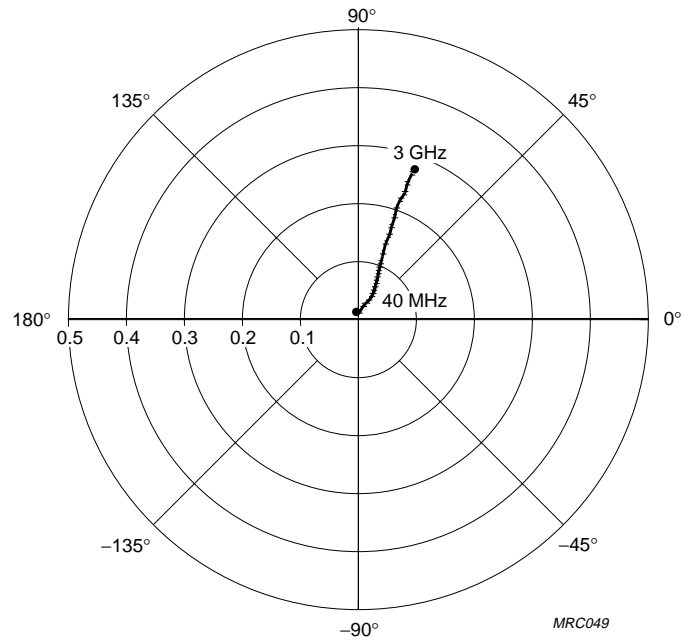


$I_C = 15 \text{ mA}$; $V_{CE} = 8 \text{ V}$.

Fig.13 Common emitter forward transmission coefficient (S_{21}).

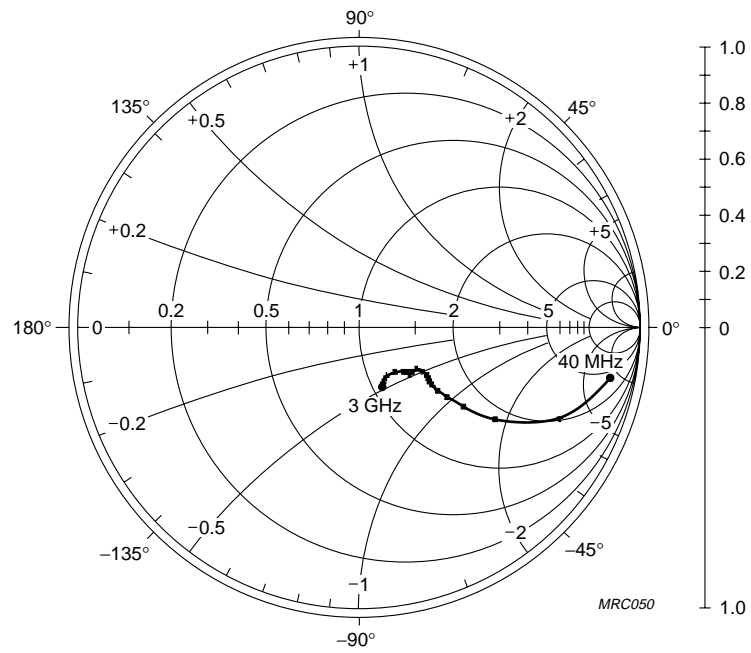
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$I_C = 15 \text{ mA}; V_{CE} = 8 \text{ V}.$

Fig.14 Common emitter reverse transmission coefficient (S_{12}).



$I_C = 15 \text{ mA}; V_{CE} = 8 \text{ V}; Z_0 = 50 \Omega.$

Fig.15 Common emitter output reflection coefficient (S_{22}).

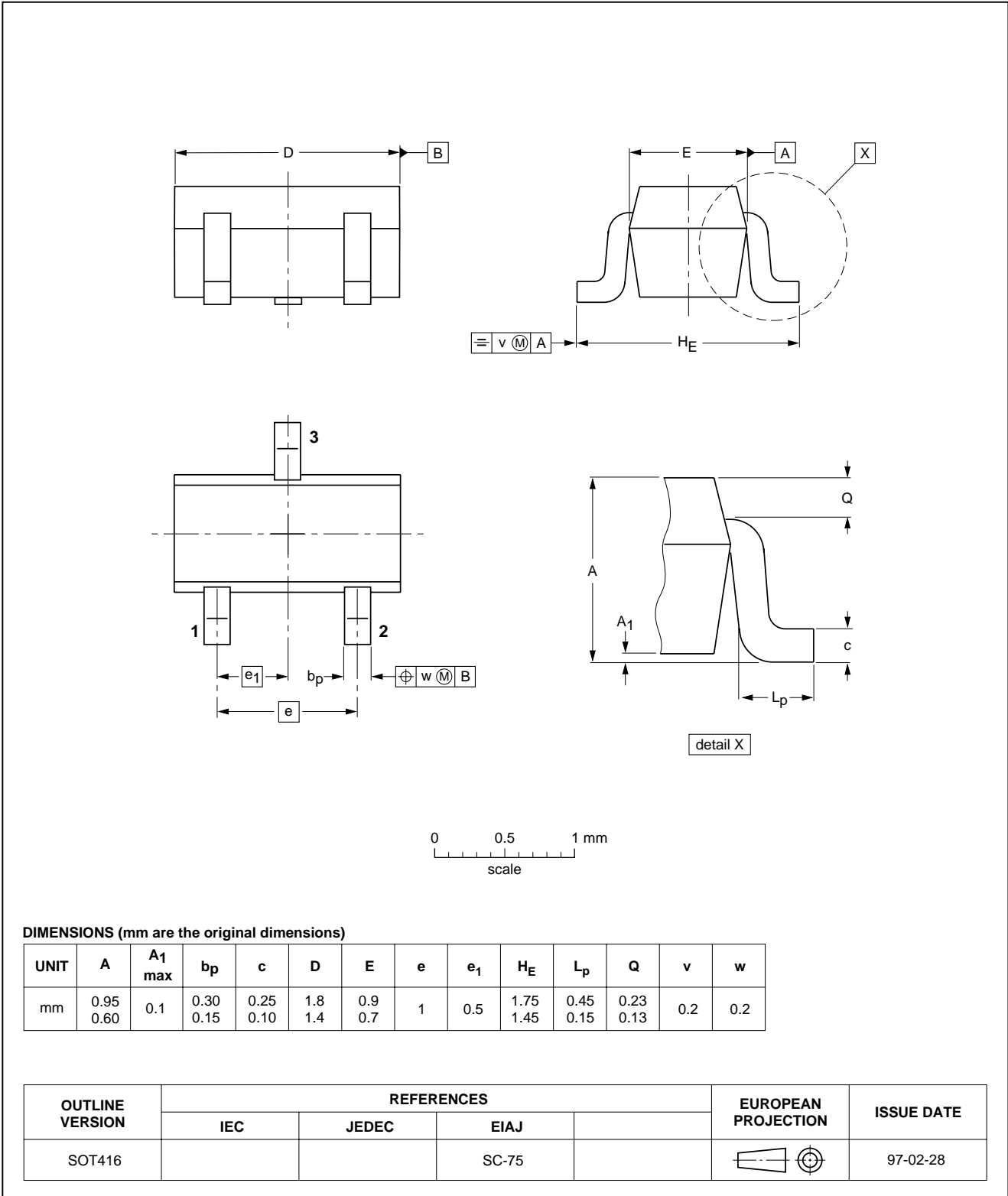
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT416



NPN 8 GHz wideband transistor

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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